

Oki.202  
09/754,264

pattern etching said Al layer.

18. (Newly Added) A method as recited in claim 17, wherein said Al layer is deposited at a temperature of at least 400 °C.

19. (Newly Added) A method as recited in claim 17, wherein said substrate is annealed at a temperature of at least 400 °C.

20. (Newly Added) A method as recited in claim 17, wherein said Al<sub>3</sub>Ti layer is deposited at a temperature of at least 400 °C.

### Remarks

#### **Status of the Claims**

Upon entry of the present amendment, claims 10-20 are pending in the present application. Claims 10, 13, and 17 are the independent claims.

#### **Rejection Under 35 U.S.C. § 103(a)**

Claims 1-9 were rejected under 35 U.S.C. § 103(a) as being unpatentable in view of *Wang* (U.S. Patent 5,604,155). As stated in the Preliminary Amendment, these claims have been canceled, and as such, this rejection is moot. For at least the following reasons, newly added claims 14-20 are believed to define over the reference to *Wang*.

Newly added claims 14 and 17 each include the preambular limitation of "A method of forming a wiring film..." The method usefully prevents pattern defects at the

Oki.202  
09/754,264

time of etching (e.g., of the Al layer) that may result in short circuits between the wires.

The reference to *Wang* contrastingly is drawn to the forming of a conductive plug (via) for contacting the source and drain regions of a metal-oxide-semiconductor (MOS) device. Clearly, these conductive plugs are not the wiring film of an integrated circuit, but rather are inter-level contacts.

Accordingly, for at least the reasons discussed above, claims 14 and 17 are believed to be allowable over the reference to *Wang*. Moreover, the claims that depend from claims 14 and 17 are also believed to be allowable. Allowance is earnestly solicited.

#### Conclusion

Withdrawal of all objections and rejection is respectfully requested. Allowance of all pending claims is earnestly solicited.

In the event that there are any outstanding matters remaining in the present application, the Examiner is invited to contact William S. Francos, Esq. (Reg. No. 38,456) at (610) 375-3513 to discuss these matters.

Except as otherwise stated in the previous Remarks, applicants note that each of the amendments have been made to place the claims in better form for U.S. practice or to clarify the meaning of the claims; not to distinguish the claims from prior art references,

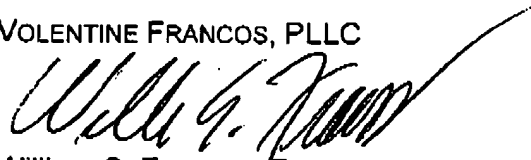
Oki.202  
09/754,264

otherwise narrow the scope or comply with other statutory requirements. Moreover, Applicants reserve all rights they may have under the Doctrine of Equivalents.

If necessary, the Commissioner is hereby authorized in this, concurrent, and future replies, to charge payment or credit any overpayment to Deposit Account No. 50-0238 for any additional fees required under 37 C.F.R. § 1.16 or under 37 C.F.R. § 1.17; particularly, extension of time fees.

Respectfully submitted,

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